

Silicon NPN Power Transistors

BD895/897/899/901

DESCRIPTION

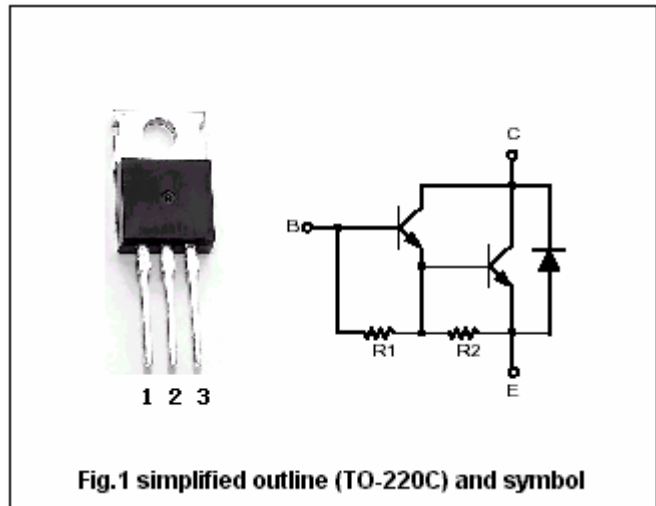
- With TO-220C package
- Complement to type BD896/898/900/902
- DARLINGTON

APPLICATIONS

- For use in output stages in audio equipment ,general amplifier,and analogue switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BD895	45	V
		BD897	60	
		BD899	80	
		BD901	100	
V_{CEO}	Collector-emitter voltage	BD895	45	V
		BD897	60	
		BD899	80	
		BD901	100	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current-DC		8	A
I_B	Base current		300	mA
P_T	Total power dissipation	$T_C=25^\circ$	70	W
		$T_a=25^\circ$	2	
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-65~150	$^\circ$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BD895	I _C =100mA, I _B =0			V
		BD897				
		BD899				
		BD901				
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A, I _B =12mA			2.5	V
V _{BE}	Base-emitter on voltage	I _C =3A; V _{CE} =3V			2.5	V
I _{CBO}	Collector cut-off current	BD895	V _{CB} =45V, I _E =0 T _C =100°C			mA
		BD897				
		BD899				
		BD901				
I _{CEO}	Collector cut-off current	BD895	V _{CE} =30V, I _B =0			0.5
		BD897				
		BD899				
		BD901				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			2	mA
h _{FE}	DC current gain	I _C =3A; V _{CE} =3V	750			
V _{EC}	Diode forward voltage	I _E =8A			3.5	V
t _{on}	Turn-on time	I _C =3A; I _{B1} =-I _{B2} =12mA V _{BE} =-3.5V; R _L =10Ω; t _p =20μs		1		μs
t _{off}	Turn-off time			5		μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.79	°C/W

PACKAGE OUTLINE

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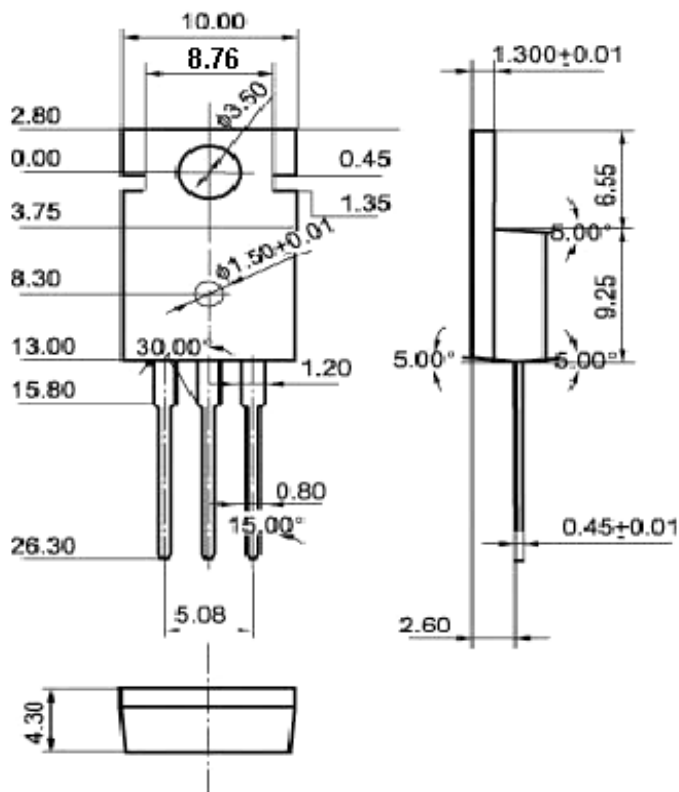


Fig.2 Outline dimensions